



2370-13

School and Training Course on Dense Magnetized Plasma as a Source of Ionizing Radiations, their Diagnostics and Applications

8 - 12 October 2012

Designing Procedure and Issues in the Development of Low Energy Fast Miniature Plasma Focus Device as Neutron and SXR Source

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• NTU ACRF Tier1 Research Grant

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	Device – location	Energy (kJ)	Peak current (kA)	Neutron Yield (neutrons/shot)	Energy density parameter (J m ⁻³)	Speed factor (kA cm ⁻¹ mbar ^{-1/2})
Mega-Joule	PF-1000 – Poland	1064	2300	2×10^{11}	1.6×10^{10}	73.4
(≥ MJ) {	FRASCATI – Italy	1000	1850	5 × 10 ¹¹	5.46 × 10 ¹⁰	69.10
\wedge	TAMU – USA	480	1400	2.6×10^{11}	10×10^{10}	76.77
	SPEED2 – Germany	187	4000	1×10^{11}	2.42×10^{10}	421.63
(10 – 500kJ)	PF-360 – Poland	130	1200	$3.8 imes 10^{10}$	$1.7 imes 10^{10}$	84.51
	DENA – Iran	90	2800	1.2×10^{9}	0.16 × 10 ⁹	98.23
\checkmark	DPF-40 – China	18	350	2.1×10^{8}	1.53×10^{10}	60.20
\wedge	7 kJ PF – Japan	7	400	$5.8 imes 10^8$	3.65×10^{10}	93.31
4	GN1 – Argentina	4.7	350	3 × 10 ⁸	1.91 × 10 ¹⁰	92.10
Medium	FN II – Mexico	4.6	350	3 × 10 ⁸	0.82×10^{10}	72.78
(2 - 10 kJ)	UNU/ICTP	2.9	170	1.2×10^{8}	9.5 × 10 ¹⁰	61.37
	<u>NX2</u>	2.9	410	7×10^8	5.3 × 10 ¹⁰	79.72
Į Ļ	BARC – India	2.2	180	14.4×10^{7}	5.32 × 10 ¹⁰	68.84
Sub-	PACO – Argentina	2	250	5 × 10 ⁸	0.35×10^{10}	81.64
kiloioule 🗪	PF-400-Chile	0.4	127	1.05 × 10 ⁶	5.2×10^{10}	70
20	03					





Device PF-400J PF-50J		PF-50J	NF
Capacity (nF)	880	160	5
Charging voltage (kV)			
Maximum	35	35	15
Typical operation	30	25-30	5-10
Inductance (nH)	38	38	5
Time to peak current (ns)	300	150	16
Stored energy (J)			
Maximum	540	100	0.56
Typical operation	400	50-70	0.1
Peak current (kA)			
Maximum	168	70	15
Typical operation	127	50-60	5-10
Maximum repetition rate (Hz)	1	1	50
Typical operation	single shot	single shot	1-20
Neutron yield per shot	1.1x10 ⁶ at 400J and 9mbar in D₂	3.3x10 ⁴ at 70J and 9mbar in D₂ 1.1x10 ⁴ at 50J and 6mbar in D₂	10 ³ with low reproducibility

P.Silva et al, RSI, 73, 2583, 2002.P. Silva et al, APL, 83, 3269, 2003J. Moreno et al, PSST, 12, 39, 2003

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I. Phys.	D: Appl.	Phys. 37	3266-76

S.M. Hassan, T. Zhang, A. Patran, R. S. Rawat, S. V. Springham, T. L. Tan, D. Wong, W. Wang, S. Lee, V.A. Gribkov, S.R. Mohanty and P. Lee, *Pinching evidences in a miniature plasma focus with fast pseudospark switch*, Plasma Sources Science and Technology 15 (4), 614-619 (2006).

Chilean Nuclear Energy Commission, CCHEN.



Why Miniature DPF? - Reason 1





Dense plasma focus for production-level EUV lithography

B. Nikolaus, W.N. Partlo, I.V. Fomenkov, Cymer Inc., San Diego, California

overview

Optical lithography will be replaced by a nonoptical technique at some point for device shrinks to 35nm. Extreme ultraviolet lithography is currently showing the most promise. However, issues such as power scaling and cost of consumables, necessary for a production-level source, are still works in progress. Cymer is proposing a concept for a 13.5nm source based on dense plasma focus to meet these challenges.





A Dense Plasma Focus device has been identified as a source for EUV lithography because

- (i) possible tuning of plasma temperature for desired EUV emission at 13.5 nm
- (ii) high source brightness,
- (iii) possible high repetition rate operation, and
- (iv) PF based sources are expected to offer lower cost of ownership in comparison to synchrotron radiation sources and laser produced plasma.





- Mo/Si multilayers have high reflectivity near 13.5 nm
- Peak reflectivity near 75%, though 69% is more typical including capping layers and diffusion barriers
- Optimal layer thickness ratio:
 - $d_{Mo} / (d_{Mo} + d_{Si}) = 0.4$
 - Each layer is 3 to 4 nm!









Neutrons and γ - rays have very penetration capability

(Penetration Depth: Suitcases to sea-land containers)

Non-intrusive Interrogation - <u>Possible</u>!

Elements	H	С	N	0	Cl	С/О	C/N	Cl/O
Explosives	Low	Medium	High	Very High	Medium	Low <1	Low <1	Very Low
Narcotics	High	High	Low	Low	Medium	High >3	High >1	Very High

Material	Expected Ratio		
	C/O	N/O	
RDX	0.53	1	
TNT	1.2	0.5	
C-4	0.71	1	







Neutrons for Active Interrogation









Passive Radioactive Neutron Source (<u>Continuous</u>)

²⁵² Cf	2.1 MeV	2.6 years
²⁴¹ Am(Be)	4.5 MeV	458 years

- ➢ Handling and Storage is problem
- Energy of neutrons is constraint
- Energy spectrum is broad
- Heavy shielding requirement

Sealed Tube Neutron Source (<u>Pulsed</u>**)**



- Accelerated hydrogen isotopes impinge on deuterated/ tritium (2-10 Ci) targets
- Cost of sealed tubes is very high
- ➤ Target limits hours of operation
- Accelerator tubes cannot be re-used





The neutron yield per shot, which scales as $Y_n \sim E^2$ or $Y_n \sim I^4$, is low in low energy PF devices as the stored energy, E, and the discharge current, I, are low in low energy PF device.

Due to low capacitance used the low energy PF devices are inherently fast (few hundreds of ns) resulting in significantly short neutron pulse-width.

The short neutron pulse is desirable for time of flight measurements **to detect the location of explosives** in complex environment.

Why Miniature DPF ??? – Reason 3 NIE **TECHNOLO** UNIVERS Towards High Rep Rate HEDP Deposition Facility





NX2 - 3kJ16 Hz – 48 kW Water Cooled Anode



FMPF3 – 0.2kJ 10 Hz – 2 kW No-water cooling required

AASC, USA High Rep Rate PF

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Demonstrate the feasibility of low energy miniature plasma focus device and optimize its performance as an efficient pulsed neutron source.

Resolve the technical intricacies confronted in repetitive mode of operation.

Explore the concept of "yield enhancement by repetition".

Significant soft and hard x-ray yields for possible applications in lithography and radiography

Intense energetic ions and electrons emissions which can be used for nanostructured material synthesis









Electrical Characteristics Measurements: short circuit test



$$L_{eq} = ?; R_{eq} = ?; I_0 = ?$$

Main objectives were to determine:

















 $T = time \ period$





1. Selection of efficient and robust devices at the component level.

- ✓ Capacitors: high energy density and shot life
- ✓ Switches: large coulomb transfer capacity, fast recovery and low jitter
- ✓ Chargers: high wattage constant power chargers for fast charging.



Intricacies in Repetitive Pulsed Power System....Contd

2. Deciding the integration and control scheme at the system level.

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(Operation and control scheme implemented in FMPF-3 device)

- Intricacies in Repetitive Pulsed Power System....Contd
 - 3. Effective interface to deliver fast pulses at <u>application level</u>.

Capacitors ----- Switch ----- Load









Roles of Three Different Versions of FMPF







The FMPF-1 device



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Capacitor bank Integrated System

Schematic View

Rishi Verma, M. V. Roshan, F. Malik, P. Lee, S. Lee, S. V. Springham, T. L. Tan, M. Krishnan and R. S. Rawat, *Compact sub-kilojoule* range fast miniature plasma focus as portable neutron source, Plasma Sources Science and Technology, 17(4), 045020 (2008).

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The FMPF-2 device





Layout of the capacitor bank

Constructional layout of FMPF-2 device

Rishi Verma, R. S. Rawat, P. Lee, M. Krishnan, S. V. Springham and T. L. Tan, *Realization of enhancement in time averaged neutron yield by using repetitive miniature plasma focus device as pulsed neutron source*, **J. Phys. D: Appl. Phys.**, 42, 235203, (2009).

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The FMPF-3 device



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Fully Integrated System

Schematic View

Rishi Verma, R. S. Rawat, P. Lee, S. V. Springham and T. L. Tan, *High performance high repetition rate miniature plasma focus device: Record time averaged neutron yield at 200 J with enhanced reproducibility*, Journal of Fusion Energy, In Press (2012).: DOI: 10.1007/s10894-012-9517-5.

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Specifications	FMPF-1	FMPF-2	FMPF-3
Total capacitance	2.4µF	2.4µF	2.4µF
Capacitance $(C_o) \times No.$ of Capacitors	(0.6μF × 4)	$(0.3\mu F \times 8),$	0.3μF × 8),
Max. charging voltage (V _o)	30kV	30kV	30kV
ESL/ESR of capacitor(s)	~70nH/ ~250mΩ	~20nH/ ~80mΩ	~20nH/ ~80mΩ
No. of energy transfer switch(s)			4
Switch type/	Trigatron/	Trigatron/	Pseudospark/
Model	Indigenous	SG-101M-75C	TDI1-150k/25
Operating voltage range/	8 – 18kV/	10 – 40kV/	3 – 20kV/
Maximum current handling limit	100kA	100kA	150kA
Max. discharge repetition rate (PRR)	0.5Hz	10Hz	10Hz





Major electrical characteristics of FMPF devices



Electrical Parameters	FMPF-1	FMPF-2	FMPF-3
Energy bank capacitance (C_o)	2.4µF	2.4µF	2.4µF
Max. charging voltage (V_o)	14kV	14kV	14kV
Max. stored energy (E_o)	235J	235J	235J
Peak short circuit current (<i>I</i> _{sc}) @ 14kV	87kA	89kA	103kA
Eq. circuit inductance (L_{eq})	27±2nH	(56±3nH)	(34±2nH)
Eq. circuit resistance (R_{eq})	(66±3mΩ)	26±3mΩ	(23±3mΩ)
Driver impedance (Z_o)	~161mΩ	~157mΩ	~106mΩ
Reversal factor (k)	33%	77%	78%
Quarter time period (T/4)	~400ns	~575ns	~458ns
Max. discharge repetition rate (PRR)	0.5Hz	10Hz	10Hz





Comparison of peak discharge currents in FMPF devices





while operating at similar energies/ charging voltages, the peak discharge current delivered by FMPF-3 device is ~18-20% higher in comparison to the two other versions of FMPF devices.

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1. Device operation is inherently fast

 $(t_{1/4} \sim 400 \text{ns and } t_{pinch} \sim 10 - 15 \text{ns})$

Requires high bandwidth response electrical diagnostics for event observation

2. Measuring Neutron Yields $\leq 10^6$ n/s

Requires customization of high sensitivity neutron detection setup

3. Generation of intense electromagnetic noise

Effective shielding of implemented diagnostics is very important



Neutron Diagnostics at PRSL



Bubble Detectors



Figure 1. Schematic of the set-up for the total neutron yield measurement from the plasma focus device.

Indium Foil Activation Detector

(for single shot operations)

Beryllium Activation Detector

(for repetitive; up to 3 Hz)

S. Mahmood, S.V. Springham, T. Zhang, R.S. Rawat, T.L. Tan, M. Krishnan, F.N. Beg, S. Lee and P. Lee, *A novel fast neutron activation counter for high repetition rate measurements*, Review Scientific Instruments 77 (10), 100713 (2006).

³He Proportional Counter

He-3 Detector Tubes

RS-P4-1636-203 (2" x 36")

$n + {}^{3}He \rightarrow {}^{3}H (573 keV) + {}^{1}H (192 keV)$

Time resolved neutron and HXR



(NE102A Scintillator Photomultiplier)

Solid State Nuclear Track Detector



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Diagnostics



Electrical



(Showing installation of Rogowski coil)

Soft X-rays



High Rep Rate Shadowgraphy System











Construction features of 'FMPF-1'





Rishi Verma, P. Lee, S V Springham, T L Tan and R S Rawat, *High Performance Thyratron Driver with Low Jitter*, Review Scientific Instruments 78 (8), 086107 (2007).

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0.2m × 0.2m × 0.5m



Fully Integrated System

Main electrical characteristics of F	MPF-1 device.
Energy bank capacitance (C_o)	2.4µF
Maximum charging voltage (V_o)	14kV
Maximum stored energy @14kV (E_o)	235J
Maximum current (under short circuit)	87kA@14kV
(I_{sc})	
Typical operating voltage range	12 – 14 kV
Eq. circuit inductance (L_{eq})	27±2nH
Eq. circuit resistance (R_{eq})	66±3mΩ
Voltage Reversal (k)	33%
Quarter time of discharge (<i>T</i> /4)	~400ns
Maximum discharge repetition rate	0.5Hz
(DRR)	



Anode designs experimented







Rishi Verma, M. V. Roshan, F. Malik, P. Lee, S. Lee, S. V. Springham, T. L. Tan, M. Krishnan and R. S. Rawat, *Compact sub-kilojoule* range fast miniature plasma focus as portable neutron source, **Plasma Sources Science and Technology**, 17(4), 045020 (2008).

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First results of neutrons and hard X-ray emission from FMPF-1



(170J, 12kV, 70kA, composite anode, tubular cathode)



Rishi Verma, M. V. Roshan, F. Malik, P. Lee, S. Lee, S. V. Springham, T. L. Tan, M. Krishnan and R. S. Rawat, *Compact sub-kilojoule range fast miniature plasma focus as portable neutron source*, **Plasma Sources Science and Technology**, 17(4), 045020 (2008).

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Neutron yield enhancement: D2-Kr admixture operation





Rishi Verma, P. Lee, S. Lee, S.V. Springham, T.L. Tan, M. Krishnan and R.S. Rawat, Order of magnitude enhancement in neutron emission with Deuterium-Krypton admixture operation in miniature plasma focus device, Applied Physics Letters **93** (10), 101501 (2008).

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Experiments with Deuterium-Krypton Admixtures



(Anode: composite, cathode: tubular)







X-ray yield enhancement: D2-Kr admixture operation



300

250

200

150

100

50

0

(us)

duration

Focusing



Figure 2. X-ray yields in the spectral range of 0.9keV to 1.6keV (SXR) and 3.2keV to 7.7keV (MXR) for D_2 and D_2 -kr admixture at different filling pressures

Figure 3. Focusing peak amplitude and Focusing duration for D_2 and D_2 -kr admixture

APPLIED PHYSICS LETTERS 92, 011506 (2008) Order of magnitude enhancement in x-ray yield at low pressure deuterium-krypton admixture operation in miniature plasma focus device

Rishi Verma,^{a)} P. Lee, S. V. Springham, T. L. Tan, and R. S. Rawat^{b)} NSSE, National Institute of Education, Nanyang Technological University, 1 Nanyang Walk, Singapore 637616, Singapore





Neutron yield enhancement: Squirrel Cage Cathode





Rishi Verma^{a,1}, R.S. Rawat^{a,*}, P. Lee^a, S. Lee^a, S.V. Springham^a, T.L. Tan^a, M. Krishnan^b

Fig. 4. Time to pinch versus D₂ filling gas pressure for tubular and squirrel cage cathode operation.

Pressure (mbar)

0

1

2

10



Neutron yield anisotropy in FMPF-1





Figure 5. Variation in axial, radial and total neutron flux with filling gas pressure.



Figure 8. Variation of HXR and neutron anisotropy as a function of pressure.



Plasma Phys. Control. Fusion 51 (2009) 075008 (16pp)

Experimental study of neutron emission characteristics in a compact sub-kilojoule range miniature plasma focus device

Rishi Verma^{1,2}, R S Rawat^{1,4}, P Lee¹, M Krishnan³, S V Springham¹ and T L Tan¹



Parameters of 'FMPF-2' device







Main electrical characteristics of 'FM	PF-2' device.
Energy bank capacitance (C_o)	2.4µF
Maximum charging voltage (V_o)	14kV
Maximum stored energy @14kV (E_o)	235J
Maximum current (under short circuit) (I_{sc})	89kA@14kV
Typical operating voltage range	12 – 14 kV
Eq. circuit inductance (L_{eq})	56±3nH
Eq. circuit resistance (R_{eq})	26±3mΩ
Voltage Reversal (f)	77%
Quarter time of discharge $(T/4)$	~575ns
Maximum discharge repetition rate (DRR)	10Hz

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Results from FMPF-2











Figure 5. Time to pinch at different repetition rates for 6 mbar D₂ filling gas pressure.

Rishi Verma, R. S. Rawat, P. Lee, S. V. Springham, T. L. Tan and M. Krishnan, *Realization of enhancement in time averaged neutron yield by using repetitive miniature plasma focus device as pulsed neutron source*, Journal of Physics D: Applied Physics **42**, 235203 (2009).

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Parameters of 'FMPF-3' device





Main electrical characteristics of 'FMPF-3'			
Energy bank capacitance (C_o)	2.4µF		
Maximum charging voltage (V_o)	14kV		
Maximum stored energy	235J		
$@14 kV(E_o)$			
Maximum current (under short	103kA		
circuit) (<i>I</i> _{sc})	@14kV		
Typical operating voltage range	10 – 14 kV		
Equivalent circuit inductance	34±2nH		
(L_{eq})			
Equivalent circuit resistance	23±3mΩ		
(R_{eq})			
Voltage Reversal (f)	78%		
Quarter time of discharge $(T/4)$	~458ns		
Maximum discharge repetition	10Hz		
rate (DRR)			



Some Results from FMPF-3





Maximum peak currents (under short circuit test conditions) in FMPF devices at different charging voltages.



Average neutron yield and time to pinch/ focus for FMPF-3 for composite anode that provided optimum yield for FMPF-2.



Current derivative (di/dt) and scintillator photomultiplier (PMT) detector signals at 4.5mbar D₂ filling gas pressure.



Average neutron yield and time to pinch/ focus at different D_2 gas filling pressures for FMPF-3 device with cylindrical anode.



Rishi Verma, R. S. Rawat, P. Lee, S. V. Springham and T. L. Tan, *High performance high repetition rate miniature plasma focus device: Record time averaged neutron yield at 200 J with enhanced reproducibility*, Journal of Fusion Energy, In Press (2012).: DOI: 10.1007/s10894-012-9517-5.

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Applications: HXR radiography source





Rishi Verma, R. S. Rawat, P. Lee, M. Krishnan, S.V. Springham, and T.L. Tan, *Miniature plasma focus device as a compact hard X-Ray source for fast radiography applications*, IEEE Transanctions on Plasma Science **38**(4), 652-657 (2010).

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Applications: Nanophase Soft Magnetic FeCo Thin Films





Fig. 2. Hysteresis loops of (a) samples deposited on $Si_{(100)}$ substrate using hydrogen (- \bullet -) and nitrogen (- \blacksquare -) gases, and (b) samples deposited on $Si_{(100)}$ (- \blacksquare -), $MgO_{(100)}$ (- \bullet -) and amorphous AI_2O_3 (- \blacktriangle -) using hydrogen as filling gas.

Z.Y. Pan, R.S. Rawat, R. Verma, J.J. Lin, H. Yan, R.V. Ramanujan, P. Lee, S.V. Springham, T.L. Tan, *Miniature plasma focus as a novel device for synthesis of soft magnetic FeCo thin films*, Physics Letters A **374**, 1043-1047 (2010).

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Applications: Nanophase Soft Magnetic FeCo Thin Films





Fig. 5. XRD pattern of the sample deposited on the ${\rm Si}_{(100)}$ substrate using hydrogen as filling gas.



Fig. 6. HRTEM image of the sample deposited on the $Si_{(100)}$ substrate using hydrogen as filling gas and corresponding SAD pattern in the inset.



Fig. 3. The morphological images of the FeCo samples deposited on

(a) Si(100), (b) MgO(100), (c) amorphous Al2O3 substrates, and
(d) the cross sectional view of the sample deposited on Si(100) using hydrogen as filling gas.

Z.Y. Pan, R.S. Rawat, R. Verma, J.J. Lin, H. Yan, R.V. Ramanujan, P. Lee, S.V. Springham, T.L. Tan, *Miniature plasma focus as a novel device for synthesis of soft magnetic FeCo thin films*, Physics Letters A **374**, 1043-1047 (2010).





Applications: High Deposition rate DLC Film Synthesis using FMPF-2





Fig. 3. Raman Spectra of the DLC films deposited using (a) 10, (b) 20, (c) 50, (d) 100 and (e) 200 focus deposition shots. E. Gharshebani, R. S. Rawat, R. Verma, S. Karamat, and S. Sobhanian, *Low energy repetitive miniature plasma focus device as high deposition rate facility for synthesis of DLC thin films*, Applied Surface Science 256(16), 4977-83 (2010).





Applications: High Deposition rate DLC Film Synthesis using FMPF-2





E. Gharshebani, R. S. Rawat, R. Verma, S. Karamat, and S. Sobhanian, *Low energy repetitive miniature plasma focus device as high deposition rate facility for synthesis of DLC thin films*, Applied Surface Science 256(16), 4977-83 (2010).

Fig. 5. XRD patterns obtained for DLC films deposited at a distance of 6 cm using 4977-83 (2010). different number of focus deposition shots,



Fig. 7. De-convolution of the C 1s binding energy peak of XPS spectrum of the deposited with 100 shots. The inset shows the typical XPS Survey spectrum of the same sample.

Atomic percentage			
No, of shots	с	0	Si
10	95,89	3,44	0,67
20	89,96	8,85	1.19
50	93,94	5,96	0.10
100	93,12	6,81	0.07
200	93,55	6,38	0,07



Fig. 6. (a) 10, (b) 20, (c) 50, (d) 100 and (e) 200 focus deposition (g) cross-sectional SEM for 200 focus deposition shots.

Other Critical Issues in High Rep Rate High Performance PF Devices: Synchronization of Switches



di/dt

4 PSG signals



Other Critical Issues in High Rep Rate High Performance PF Devices: Synchronization of Switches





Trigger pulse signal

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Other Critical Issues in High Rep Rate High Performance PF Devices: Thermal Load Management



Operation at high rep-rate is needed to be compensated for lower yield related for Low Energy PF devices. But higher operating frequency

- Introduces thermal management problems in the electrodes and chamber walls
- Ablation of anode tip material by electron beam and hot dense plasma
- Coaxial geometry with multiple cathode rods and a single anode

Anode thermal management is an important first step to high rep-rate operation





Other Critical Issues in High Rep Rate High Performance PF Devices: Thermal Load Management



- Simple geometry relies on thermal conductivity of anode material (Cu or SS) to conduct heat to large flange to which anode is connected. The flange holding anode act like the heat sink.
- The 2 kW FMPF facility (200J @ 10 Hz repetition rate) with assumption of about 20% being used up in heating up the anode top gives approximately 400 W/cm² thermal load into anode. But at 100 Hz operation the same will go to 4 kW/cm².
- Very little heat transfer to the low pressure gas.
- The annular design of anode also impedes the heat flow
- Active cooling would be essential

Other Critical Issues in High Rep Rate High Performanc PF Devices: High Sensitivity to Gas-fill Type



T. Zhang, X. Lin, K. A. Chandra, T.L. Tan, S.V. Springham, A. Patran, P. Lee, S. Lee and **R.S. Rawat**, Plasma Source Science and Technology **14** (1), 368-374, 2005.



S.M. Hassan, T. Zhang, A. Patran, **R. S. Rawat**, S. V. Springham, T. L. Tan, D. Wong, W. Wang, S. Lee, V.A. Gribkov, S.R. Mohanty and P. Lee, Plasma Sources Science and Technology **15** (4), 614-619 (2006).

About 20-30% of total time to pinch (breakdown to pinch) is spent in formation of well defined current sheath at the insulator sleeve.

So the time available for the formation of current sheath decreases with the decrease in the time to pinch for low energy fast PF devices.

For very fast extremely low energy plasma focus the smaller time may not be sufficient for proper current sheath formation and hence pinching efficiency will also be poor.

The smaller time available for current sheath formation may also have significant affect on the degree of ionization of various gases used. The optimized electrode dimensions may differ significantly for gases.

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